

RIDGE WAVEGUIDE LASER with AR-COATING

GaAs Semiconductor Laser Diode

Tunable Fabry-Perot Laser for External Cavity Operation



28.11.2011

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General Product Information

Product	Application
tunable 920 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	
sealed SOT Housing	
Monitor Diode	



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-20		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			180
Reverse Voltage	V_R	V			0
Output Power (extracavity)	P _{opt}	mW			50

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		40
Forward Current	I_{F}	mA			160

Measurement Conditions / Comments	

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		920	
Tuning Range	$\Delta \lambda_{\text{tun}}$	nm	880		930
Output Power (extracavity)	P_{opt}	mW		15	
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1.10-3
Polarization				TE	
Spatial Mode (transversal) TEM ₀₀					
Spectral Mode (longitudinal)		Single/Multi Mode			

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

E field parallel to Pin 2 - Pin 3 - plane Fundamental Mode depending on operating conditions



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Monitor Diode

Symbol	Unit	min	typ	max
I _{mon} / P _{opt}	μA / mW	2		40
$U_{R\ MD}$	V	3		5
	I _{mon} / P _{opt}	I _{mon} / P _{opt} μA / mW	I _{mon} / P _{opt} μA / mW 2	I _{mon} / P _{opt} μA / mW 2

Measurement Conditions / Comments
$U_R = 5 \text{ V}$; P_{opt} intracavity



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Tunable Fabry-Perot Laser for External Cavity Operation



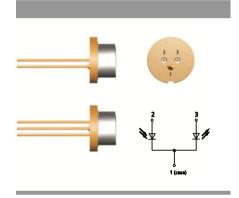
Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	I _{PIN}	mm		14	

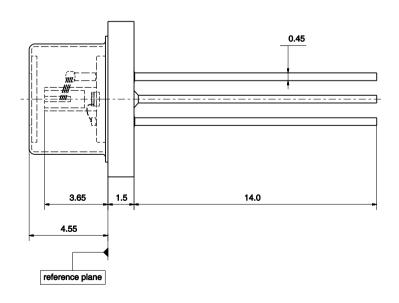
Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

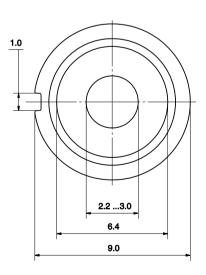
Package Pinout

Ground	1
Photo Diode (+)	2
Laser (+)	3



Package Drawings







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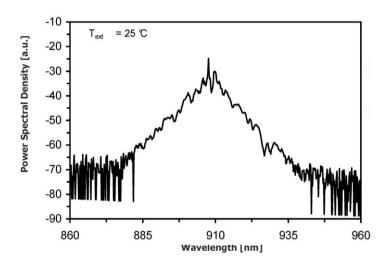
RIDGE WAVEGUIDE LASER with AR-COATING

GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



Typical Measurement Results

Emission Spectrum measured without external feedback



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWE diode type is known to be sensitive against thermal stress. It should not be operated without appropriate optical feedback from an external cavity. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

















GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



PRELIMINARY SPECIFICATION

RWE Laser

EYP-RWE-0980-08020-1500-SOT02-0000

General Product Information	
Product	Application
tunable 980 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL) sealed SOT Housing	
Monitor Diode	



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T _S	°C	-20		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			120
Reverse Voltage	V_R	V			0

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device realibility and may lead to reduced operational life.

Recommend		

	Symbol	Unit	min	typ	max
Operational Temperature at case	T _C	°C	15		40
Forward Current	l _F	mA			100

Characterist	ics at T _{amb} 25	°C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		980	
Tuning Range	$\Delta \lambda_{\text{tun}}$	nm	900		1000
Output Power (extracavity)	P_{opt}	mW		50	
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1.10-3
Polarization				TE	

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

Polarization parallel to Pin 2 - Pin 3 -plane





GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



PRELIMINARY SPECIFICATION

RWE Laser

EYP-RWE-0980-08020-1500-SOT02-0000

Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt ic}	μA / mW	1		10
Reverse Voltage Monitor Diode	$U_{R\ MD}$	V	3		5

Measurement Conditions / Comments
$U_{R MD} = 5 V$, $P_{opt ic}$: intracavity power of the ECDL



GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



PRELIMINARY SPECIFICATION

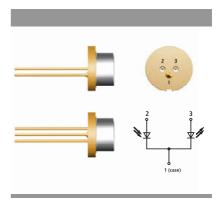
RWE Laser

EYP-RWE-0980-08020-1500-SOT02-0000

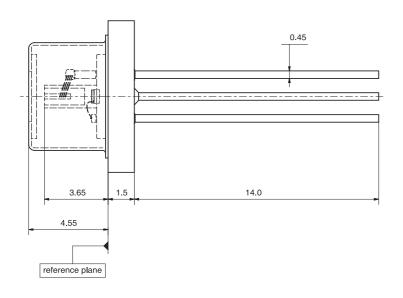
Package Dimensions					
	Symbol	Unit	min	typ	max
Emission Plane	d _{EP}	mm	3.50	3.65	3.70
Housing Diameter	d	mm		9.0	
Pin Length	I	mm		14.0	

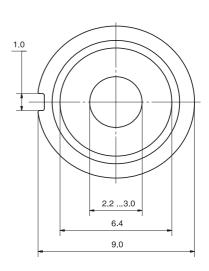
reference plane: top side of TO header

Package Pinout	M-Type	
Ground	1	
Photo Diode (+)	2	
Laser (+)	3	



Package Drawings







GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



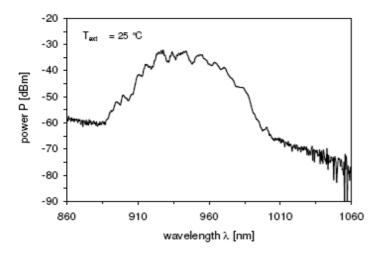
PRELIMINARY SPECIFICATION

RWE Laser

EYP-RWE-0980-08020-1500-SOT02-0000

Typical Measurement Results

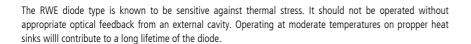
Emission Spectrum measured without external feedback



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Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase thread to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

















EYP-RWE-1060-10020-1500-SOT02-0000



Revision 1.00

GAIN CHIPS AR coated Fabry-Perot Laser



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General Product Information

Product	Application
tunable 1060 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	covering wavelengths
sealed SOT Housing	between 980 and 1090 nm
Monitor Diode	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			220
Reverse Voltage	V_R	V			0
Output Power (extracavity)	P_{opt}	mW			120

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum
Ratings can cause permanent damage to the device.
Please note that a damaging optical power level may
occur although the maximum current is not reached.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		40
Forward Current	I _F	mA			200
Output Power (extracavity)	P_{opt}	mW			100

Measurement	Conditions /	Comments
IVICasul CITICIT	Conditions /	Comments

Characteristics at 25° C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		1060	
Tuning Range	$\Delta \lambda_{\text{tun}}$	nm	980		1090
Output Power (extracavity)	P_{opt}	mW		80	
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1·10 ⁻³
Polarization				TE	
Spatial Mode (transversal) TEM ₀₀					
Spectral Mode (longitudinal)			Sin	ıgle/Multi Mo	ode
Divergence parallel (FWHM)	$\Theta_{ }$	0		10	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		24	

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

E field parallel to Pin 2 - Pin 3 - plane
Fundamental Mode
depending on operating conditions
parallel to Pin 2 - Pin 3 plane (see p. 3)
perpendicular to Pin 2 - Pin 3 plane (see p. 3)

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GAIN CHIPS AR coated Fabry-Perot Laser



Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity ($U_{RMD} = 5 \text{ V}$)	I _{mon} / P _{opt}	μA / mW		20	

Measurement Conditions / Comments
depends on the intracavity power of the ECDL setup

Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	I _{PIN}	mm		14	

Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

Package Pinout

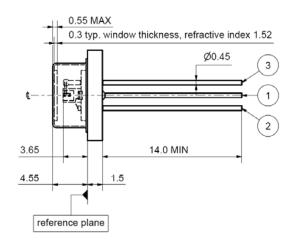
		2

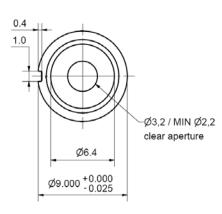
Laser Diode Cathode, Monitor Diode Cathode, Case
 Photo Diode Anode
 Laser Diode Anode

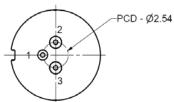




Package Drawings







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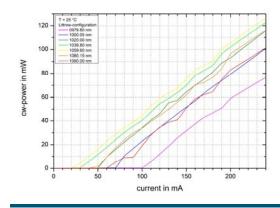


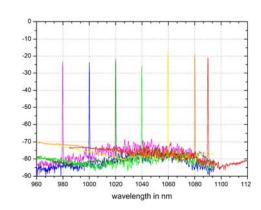
Revision 1.00

GAIN CHIPSAR coated Fabry-Perot Laser



Typical Measurement Results ex cavity





Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWE diode type is known to be sensitive against thermal stress. It should not be operated without appropriate optical feedback from an external cavity. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.















EYP-RWE-1060-10525-1500-SOT02-0000



Revision 1.00

GAIN CHIPS AR coated Fabry-Perot Laser



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General Product Information

Product	Application
widely tunable 1060 nm modified Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	covering wavelengths
sealed SOT Housing	between 960 and 1100 nm
Monitor Diode	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			220
Reverse Voltage	V_R	V			0
Output Power (extracavity)	P_{opt}	mW			120

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum
Ratings can cause permanent damage to the device.
Please note that a damaging optical power level may
occur although the maximum current is not reached.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		40
Forward Current	I _F	mA			200
Output Power (extracavity)	P_{opt}	mW			100

Measurement Conditions /	Comments

Characteristics at 25° C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		1060	
Tuning Range	$\Delta \lambda_{tun}$	nm	960		1100
Output Power (extracavity)	P_{opt}	mW		80	
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1.10-3
Polarization				TE	
Spatial Mode (transversal) TEM ₀₀					
Spectral Mode (longitudinal)			Sin	ıgle/Multi Mo	ode
Divergence parallel (FWHM)	$\Theta_{ }$	0		10	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		24	

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

E field parallel to Pin 2 - Pin 3 - plane
Fundamental Mode
depending on operating conditions
parallel to Pin 2 - Pin 3 plane (see p. 3)
perpendicular to Pin 2 - Pin 3 plane (see p. 3)

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GAIN CHIPS AR coated Fabry-Perot Laser



N.	7or	nito	r D	iod	

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity ($U_{R MD} = 5 V$)	I _{mon} / P _{opt}	μA / mW		20	

Measurement Conditions / Comments
depends on the intracavity power of the ECDL setup

Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	I _{PIN}	mm		14	

Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

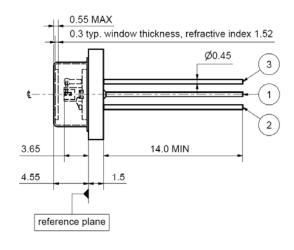
Package Pinout

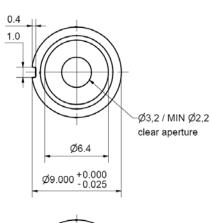
- Laser Diode Cathode, Monitor Diode Cathode, Case
 Photo Diode Anode
- 2 Photo Diode Anode3 Laser Diode Anode

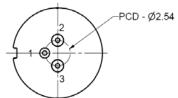




Package Drawings







EYP-RWE-1060-10525-1500-SOT02-0000

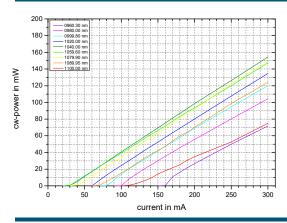


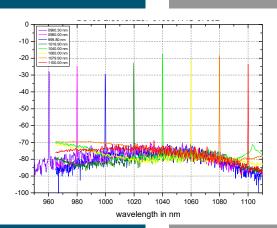
Revision 1.00

GAIN CHIPS AR coated Fabry-Perot Laser



Typical Measurement Results ex cavity





Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWE diode type is known to be sensitive against thermal stress. It should not be operated without appropriate optical feedback from an external cavity. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.

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